

AHL5218T8 Data Sheet

Ultra Low Noise Amplifier

1. Product Overview

1.1 General Description

AHL5218T8 is a low noise amplifier with very low noise and high linearity at low dc power consumption over a single matching circuit frequency of 1.2 ~ 3.0 GHz with the minimum off-chip components. It has an active bias circuit for stable current over temperature and process variation. It also has power on/off control function. The amplifier is available in TDFN8 package and passes the stringent DC, RF and reliability tests.

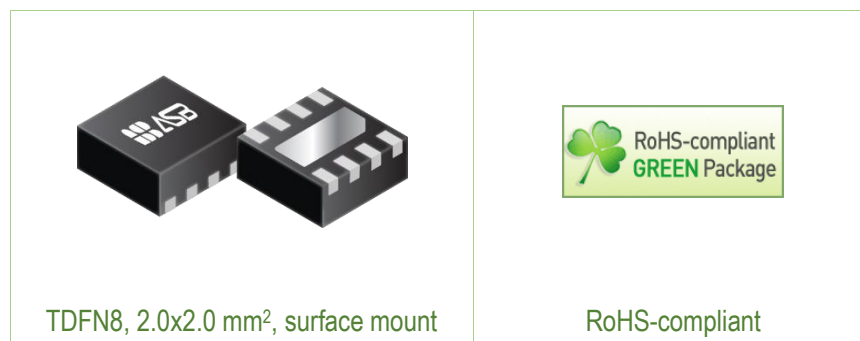
1.2 Features

- Gain decreases from 23 dB to 15 dB at 1.2~3.0 GHz (19 dB at 2.0 GHz)
- NF of 0.32~0.53 dB at 1.2~3.0 GHz (0.37 dB @ 2.0 GHz)
- 36 dBm OIP3 at 2.0 GHz
- 20 dBm P1dB at 2.0 GHz
- Integrated LNA on/off Control
- MTTF > 100 Years
- Single Supply: +5 V

1.3 Applications

- Low Noise Amplifier for L-band application
- Active Antenna
- Other Low Noise Application

1.4 Package Profile & RoHS Compliance



2. Summary on Product Performances

2.1 Typical Performance

Supply voltage = +5 V, $T_A = +25\text{ }^{\circ}\text{C}$, $Z_0 = 50\text{ }\Omega$.

Parameter	Typical										Unit
Frequency	1200	1500	1700	1900	2000	2300	2500	2700	3000		MHz
Gain	23.0	21.5	20.4	19.4	18.9	17.6	16.8	16.0	15.2		dB
S11	-9.5	-13.0	-14.0	-15.0	-15.0	-16.0	-16.0	-16.0	-16.0		dB
S22	-10.0	-17.0	-19.0	-19.0	-18.0	-14.0	-12.0	-10.0	-9.0		dB
Noise Figure ¹⁾	0.32	0.29	0.32	0.35	0.37	0.40	0.43	0.47	0.53		dB
Output IP3 ²⁾	35.0	35.5	36.0	36.0	36.0	36.0	36.0	36.0	36.0		dBm
Output P1dB	20.0	20.5	21.0	20.5	20.0	20.0	19.5	19.5	19.5		dBm
Current	65										mA
Device Voltage	5										V

1) Noise figure measured at the connectors on the board. (i.e. not de-embedded)

2) OIP3 is measured with two tones at the output power of +4 dBm/tone separated by 1 MHz.

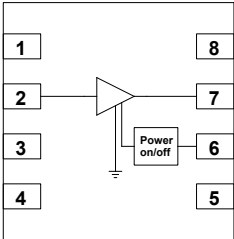
Parameter	Conditions	Min	Typ	Max	Unit
Power Shutdown Control (Vc)	On state		0		V
	Off state		1.0	Vd	V
Current	On state		65		mA
	Off state		3		mA
Switching Speed	Rise time (10% to 90%)		150		ns
	Fall time (90% to 10%)		150		ns

2.2 Product Specification

Supply voltage = +5 V, $T_A = +25\text{ }^{\circ}\text{C}$, $Z_0 = 50\text{ }\Omega$.

Parameter	Min	Typ	Max	Unit
Frequency		2000		MHz
Noise Figure		0.37		dB
Gain		18.9		dB
S11		-15.0		dB
S22		-18.0		dB
Output IP3		36.0		dBm
Output P1dB		20.0		dBm
Current		65		mA
Device Voltage		+5		V

2.3 Pin Configuration

Pin	Description	Simplified Outline
2	RF IN	
6	Vc (on/off function)	
7	RF OUT	
1, 3, 4, 5, 8	NC or GND	
Backside paddle	GND	

2.4 Absolute Maximum Ratings

Parameters	Max. Ratings
Operation Case Temperature	-40 to +85 °C
Storage Temperature	-40 to +150 °C
Device Voltage	+6 V
Operation Junction Temperature	+150 °C
Input RF Power (CW, 50 Ω matched)	+25 dBm

2.5 Thermal Resistance

Symbol	Description	Typ	Unit
R _{th}	Thermal resistance from junction to lead	90	°C/W

2.6 ESD Classification & Moisture Sensitivity Level

ESD Classification

HBM	Class 1A	Voltage Level: 250~500 V
CDM	Class C6	Voltage Level: > 1000 V

CAUTION: Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

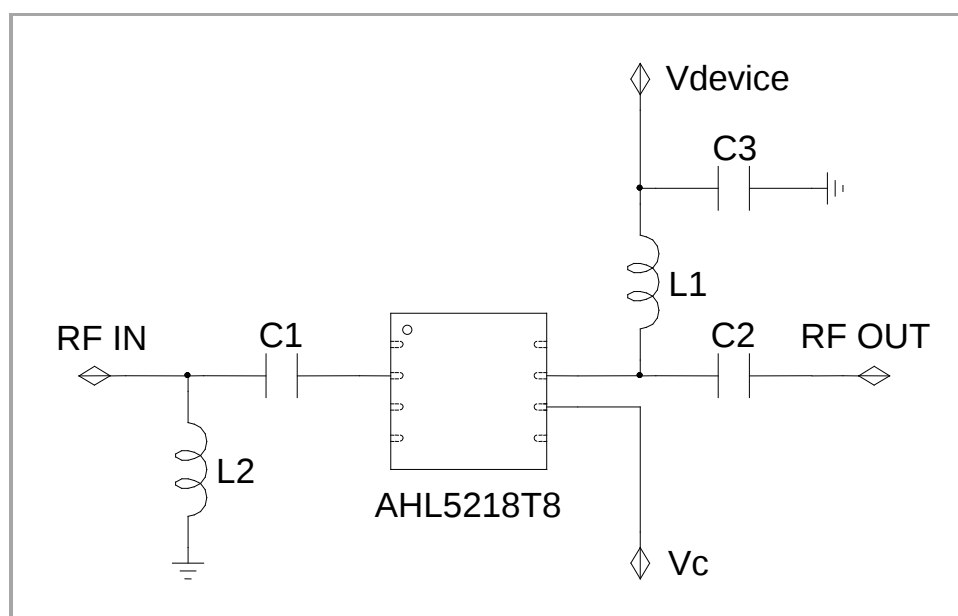
Moisture Sensitivity Level

MSL 3 at 260 °C reflow

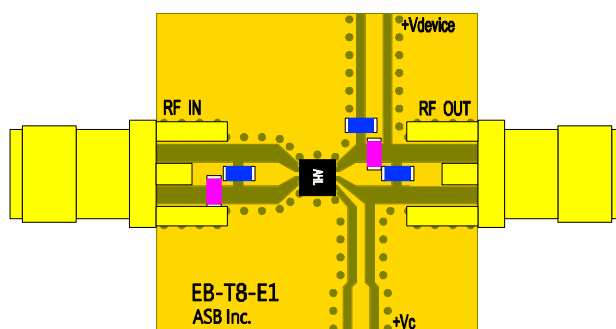
(Intentionally Blanked)

3. Application: 1200~3000 MHz ($V_{\text{DEVICE}} = +5 \text{ V}$)

3.1 Application Circuit & Evaluation Board



* Backside paddle is RF/ DC ground.



State	Vc (V)
LNA ON	0 or GND
OFF	1.0 ~ Vd
PCB Information	
Material	FR4
Thickness (mm)	0.8
Size (mm)	18x18
EB No.	EB-T8-E1

Bill of Material

Symbol	Value	Size	Description	Manufacturer
AHL5218T8	-	-	MMIC amplifier	ASB
C1	10 pF	0603	DC blocking capacitor	Murata
C2	100 pF	0603	DC blocking capacitor	Murata
C3	1 μ F	0603	Decoupling capacitor	Murata
L1	6.8 nH	0603	RF choke inductor	Murata
L2	10 nH	0603	Input matching inductor	Murata

3.2 Performance Table

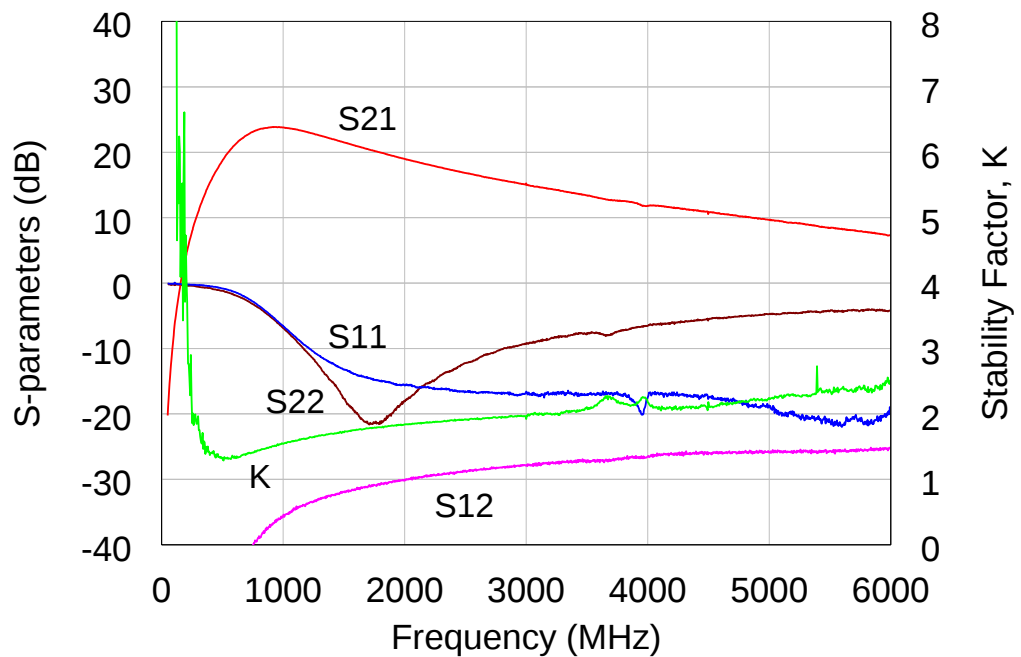
Supply voltage = +5 V, $T_A = +25\text{ }^{\circ}\text{C}$, $Z_0 = 50\text{ }\Omega$.

Parameter	Typical										Unit
Frequency	1200	1500	1700	1900	2000	2300	2500	2700	3000		MHz
Gain	23.0	21.5	20.4	19.4	18.9	17.6	16.8	16.0	15.2		dB
S11	-9.5	-13.0	-14.0	-15.0	-15.0	-16.0	-16.0	-16.0	-16.0		dB
S22	-10.0	-17.0	-19.0	-19.0	-18.0	-14.0	-12.0	-10.0	-9.0		dB
Noise Figure ¹⁾	0.32	0.29	0.32	0.35	0.37	0.40	0.43	0.47	0.53		dB
Output IP3 ²⁾	35.0	35.5	36.0	36.0	36.0	36.0	36.0	36.0	36.0		dBm
Output P1dB	20.0	20.5	21.0	20.5	20.0	20.0	19.5	19.5	19.5		dBm
Current	65										mA
Device Voltage	5										V

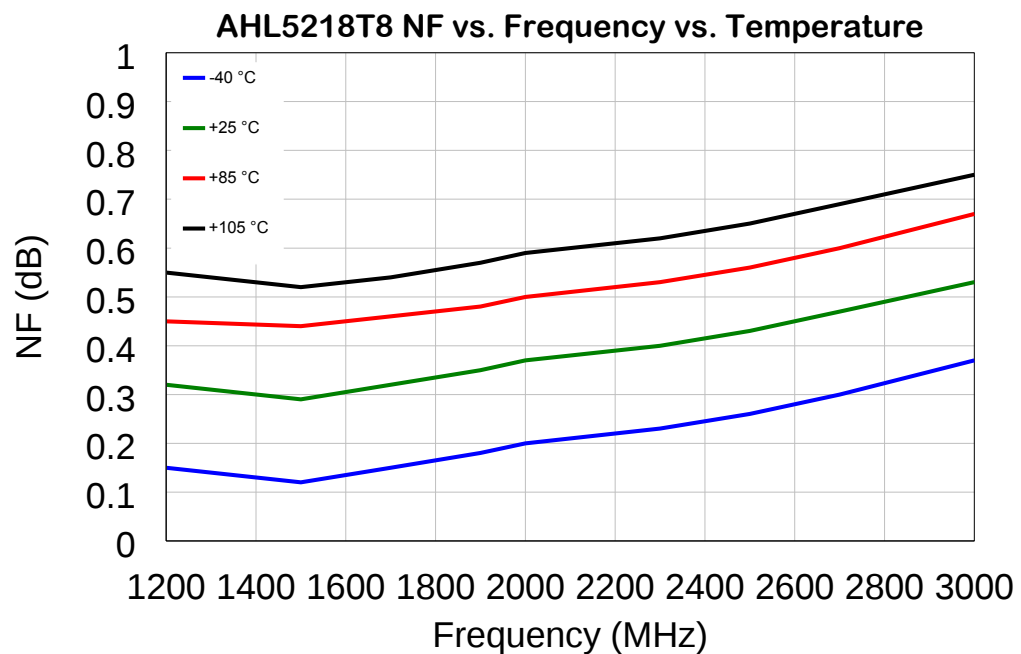
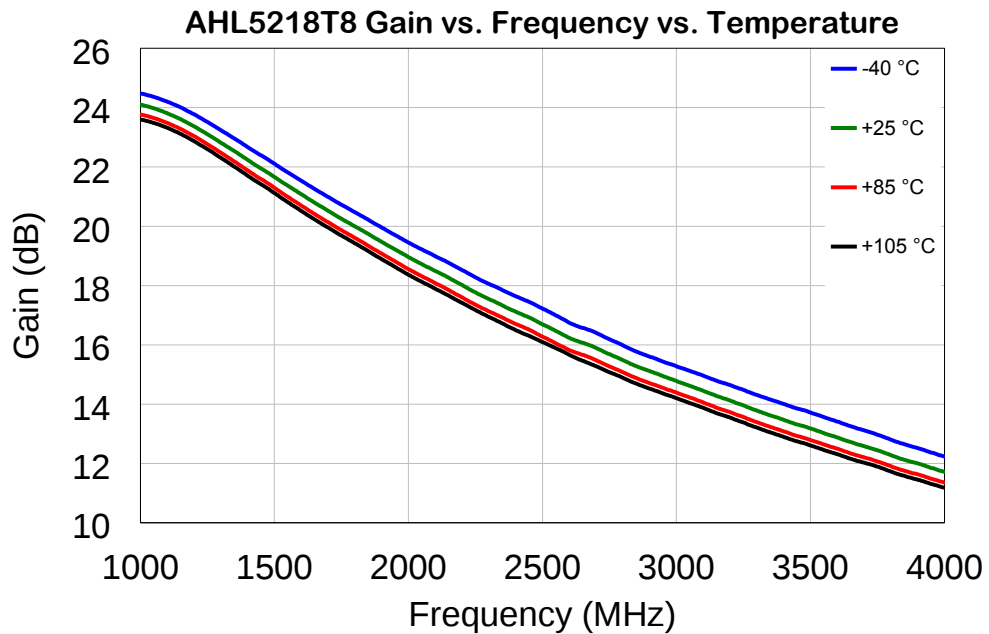
1) Noise figure measured at the connectors on the board. (i.e. not de-embedded)

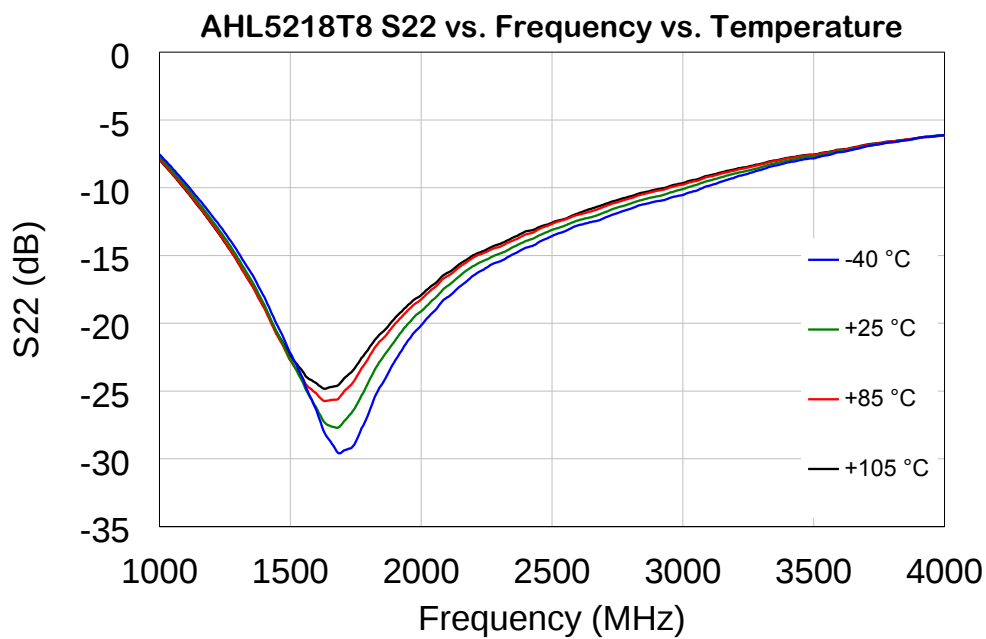
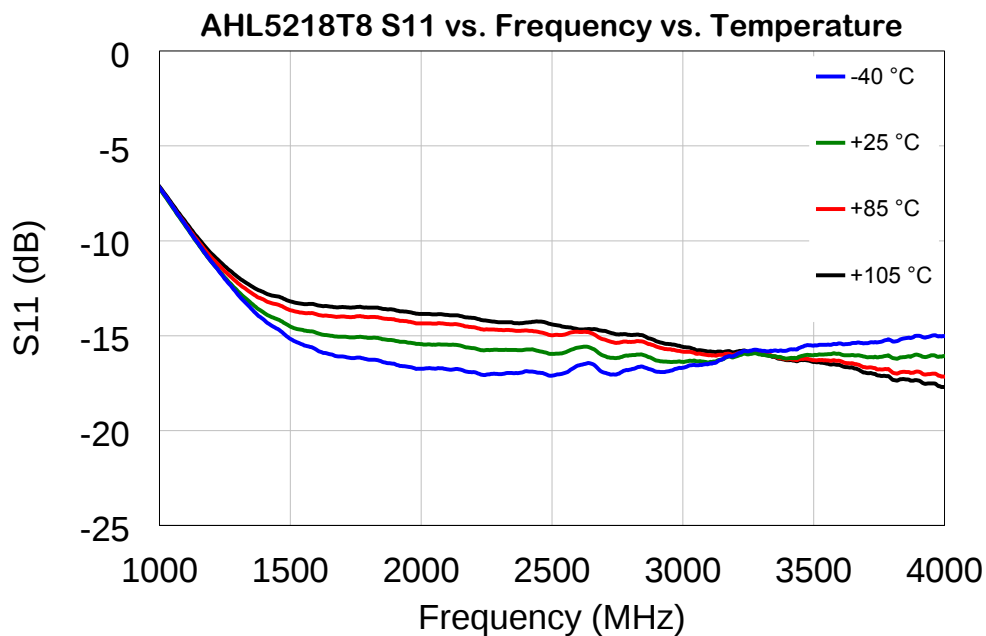
2) OIP3 is measured with two tones at the output power of +4 dBm/tone separated by 1 MHz.

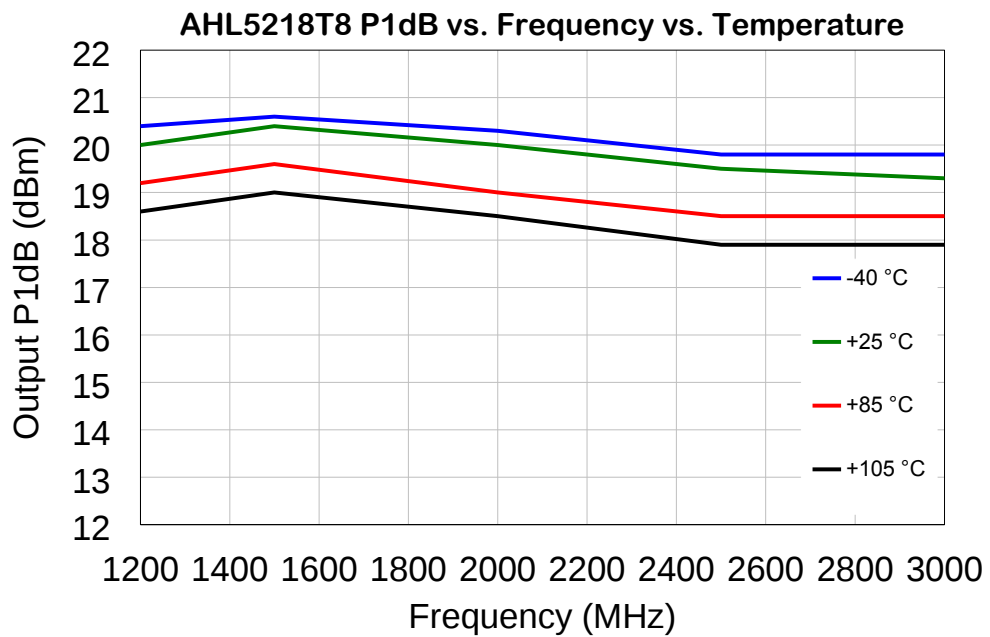
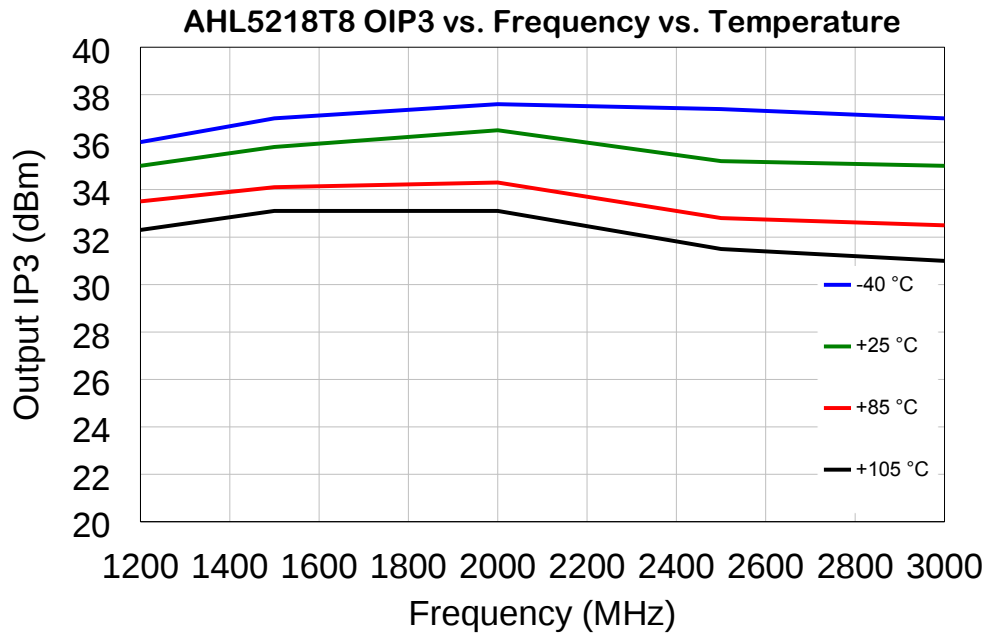
3.3 Plot of S-parameters

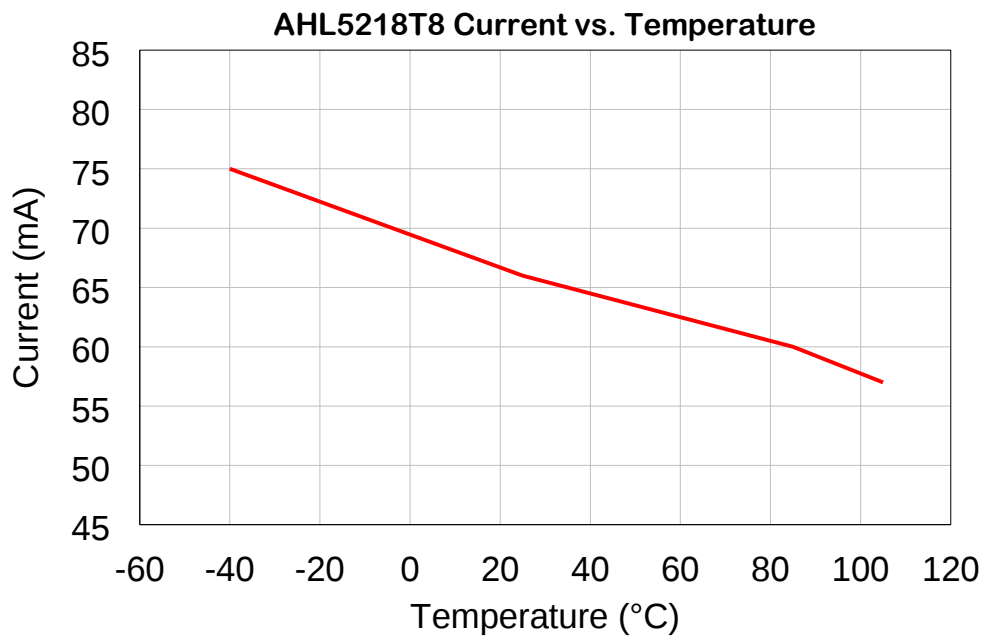
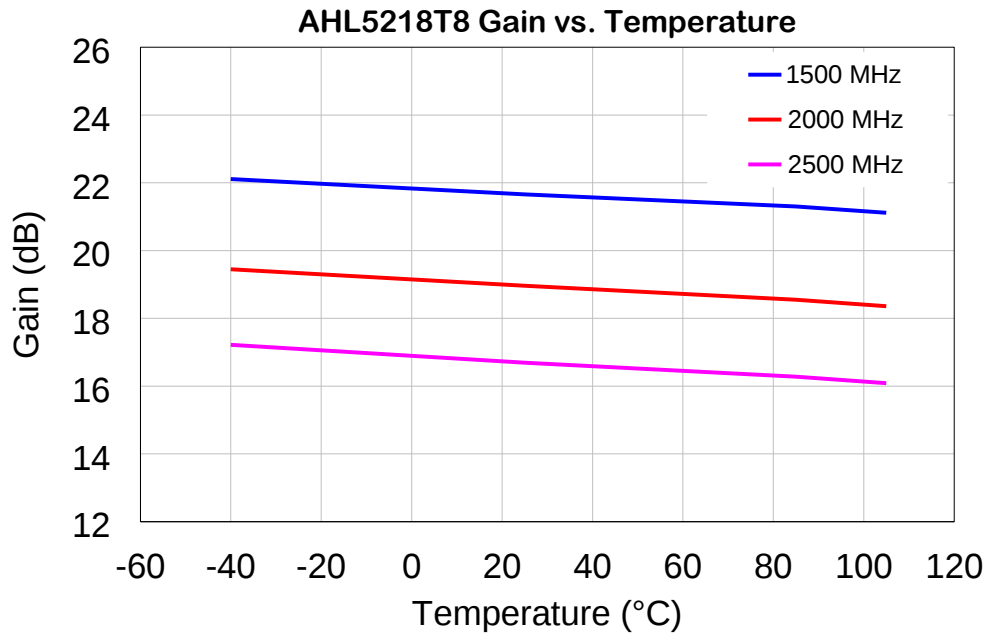


3.4 Plots of Noise Figure and Performances with Temperature



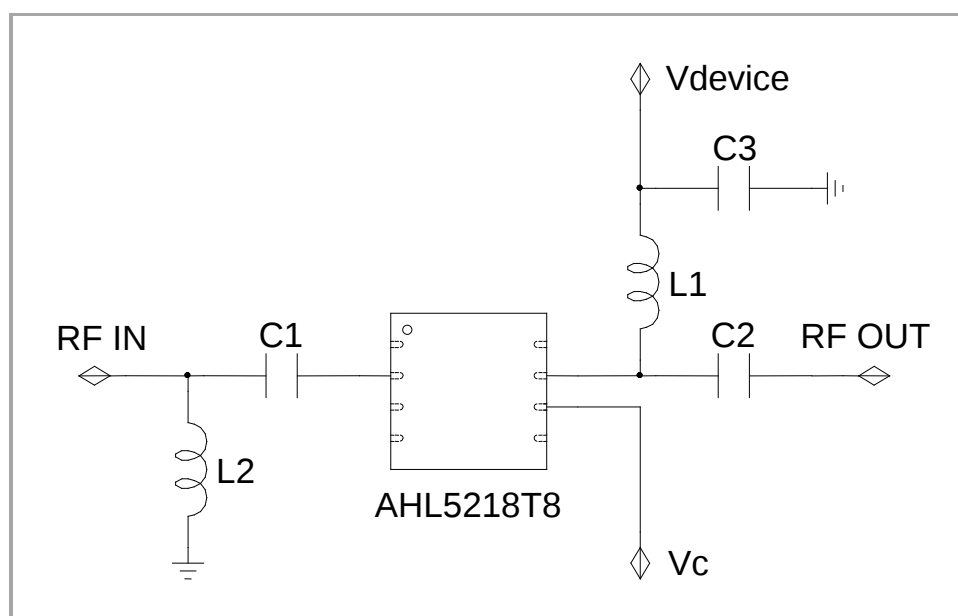




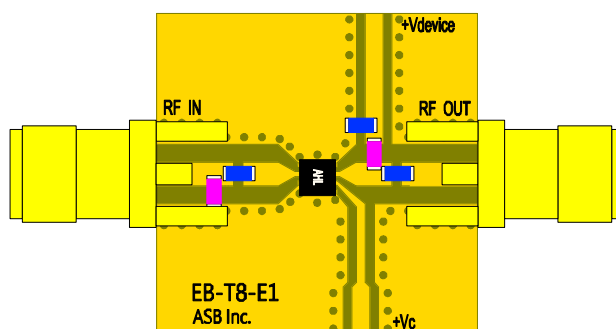


4. Application: 1500~2000 MHz ($S_{11} < -18$ dB, $V_{\text{DEVICE}} = +5$ V)

4.1 Application Circuit & Evaluation Board



* Backside paddle is RF/ DC ground.



State	Vc (V)
LNA ON	0 or GND
OFF	1.0 ~ Vd
PCB Information	
Material	FR4
Thickness (mm)	0.8
Size (mm)	18x18
EB No.	EB-T8-E1

Bill of Material

Symbol	Value	Size	Description	Manufacturer
AHL5218T8	-	-	MMIC amplifier	ASB
C1	10 pF	0603	DC blocking capacitor	Murata
C2	100 pF	0603	DC blocking capacitor	Murata
C3	1 μ F	0603	Decoupling capacitor	Murata
L1	6.8 nH	0603	RF choke inductor	Murata
L2	6.8 nH	0603	Input matching inductor	Murata

4.2 Performance Table

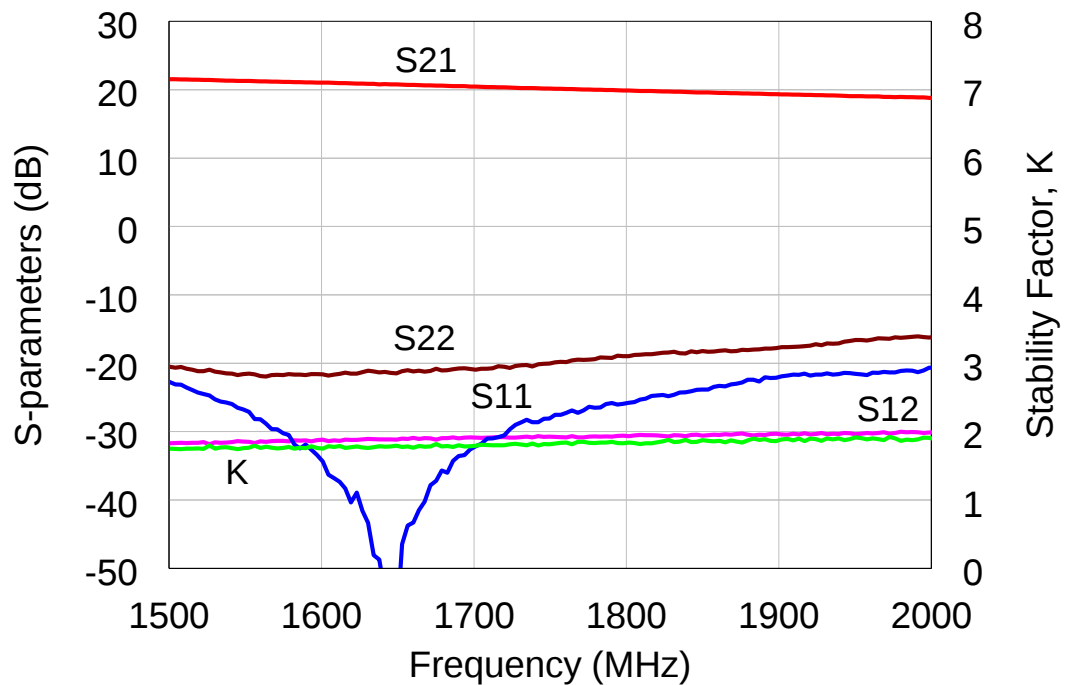
Supply voltage = +5 V, $T_A = +25\text{ }^{\circ}\text{C}$, $Z_0 = 50\text{ }\Omega$.

Parameter	Typical				Unit
Frequency	1500	1700	1900	2000	MHz
Gain	22.1	21.5	20.5	19.3	dB
S11	-20.0	-20.0	-20.0	-20.0	dB
S22	-20.0	-20.0	-17.0	-16.0	dB
Noise Figure ¹⁾	0.36	0.34	0.37	0.40	dB
Output IP3 ²⁾	35.0	35.5	36.0	36.0	dBm
Output P1dB	20.5	20.5	20.5	20.0	dBm
Current	65				mA
Device Voltage	5				V

1) Noise figure measured at the connectors on the board. (i.e. not de-embedded)

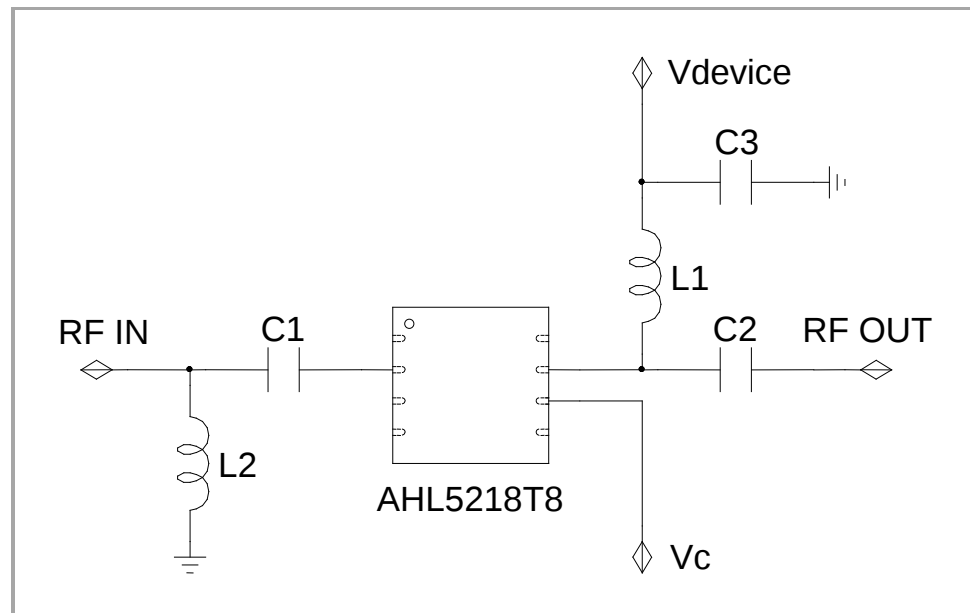
2) OIP3 is measured with two tones at the output power of +4 dBm/tone separated by 1 MHz.

4.3 Plot of S-parameters

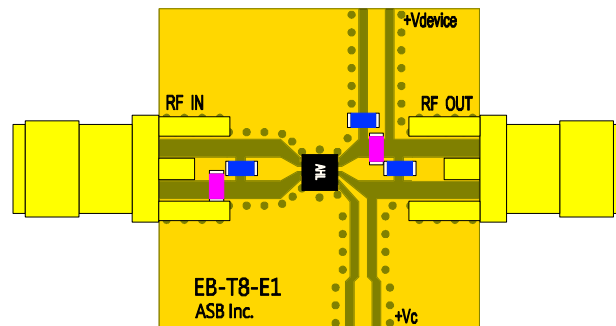


5. Application: 1100~1700 MHz ($V_{\text{DEVICE}} = +1.8, +2.7, +3.3 \text{ V}$)

5.1 Application Circuit & Evaluation Board



* Backside paddle is RF/ DC ground



State	Vc (V)
LNA ON	0 or GND
OFF	1.0 ~ Vd
PCB Information	
Material	FR4
Thickness (mm)	0.8
Size (mm)	18x18
EB No.	EB-T8-E1

Bill of Material

Symbol	Value	Size	Description	Manufacturer
AHL5218T8	-	-	MMIC Amplifier	ASB
C1	22 pF	0603	DC blocking capacitor	Murata
C2	100 pF	0603	DC blocking capacitor	Murata
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L1	10 nH	0603	RF Choke inductor	Murata
L2	6.8 nH	0603	Input matching inductor	Murata

5.2 Performance Table

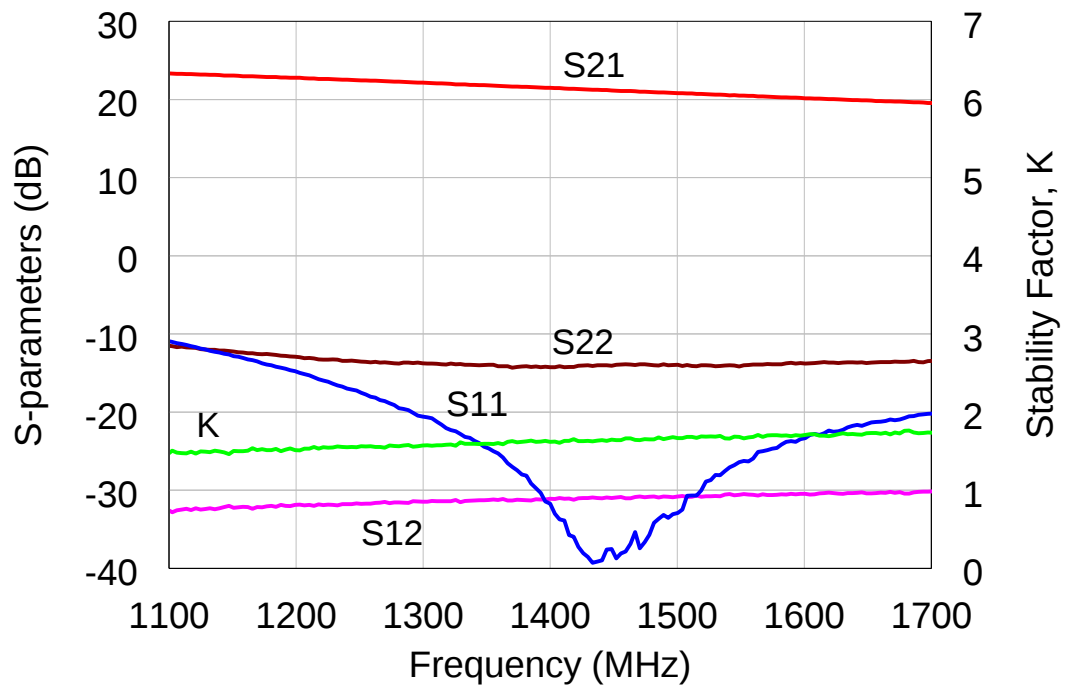
Supply voltage = +1.8, +2.7, +3.3 V, $T_A = +25\text{ }^{\circ}\text{C}$, $Z_0 = 50\text{ }\Omega$.

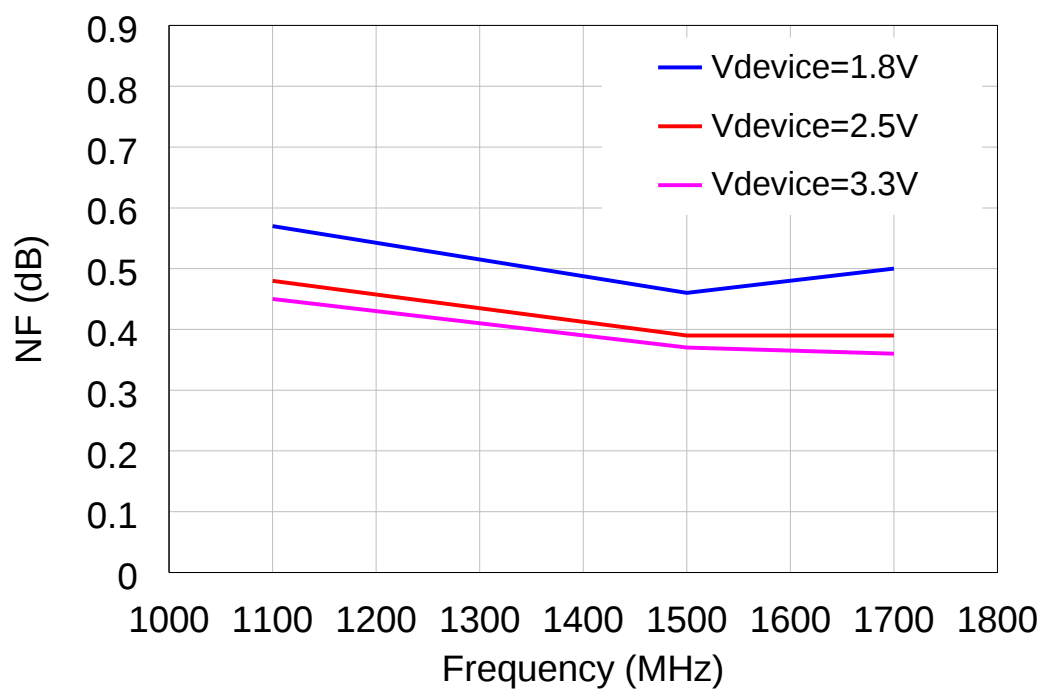
Parameter	Typical									Unit
Frequency	1100	1500	1700	1100	1500	1700	1100	1500	1700	MHz
Gain	20.8	18.0	16.6	22.8	20.2	18.9	23.3	20.8	19.6	dB
S11	-9.0	-11.0	-10.0	-11.0	-18.0	-15.0	-10.0	-18.0	-18.0	dB
S22	-10.0	-12.0	-12.0	-11.0	-13.0	-13.0	-11.0	-13.0	-13.0	dB
Noise Figure ¹⁾	0.57	0.46	0.50	0.48	0.39	0.39	0.45	0.37	0.36	dB
Output IP3 ²⁾	18.0	18.0	20.0	24.0	25.0	26.0	28.0	29.0	30.0	dBm
Output P1dB	8.0	9.0	9.0	14.0	14.0	14.0	17.0	17.0	17.0	dBm
Current	10			24			33			mA
Device Voltage	1.8			2.7			3.3			V

1) Noise figure measured at the connectors on the board. (i.e. not de-embedded)

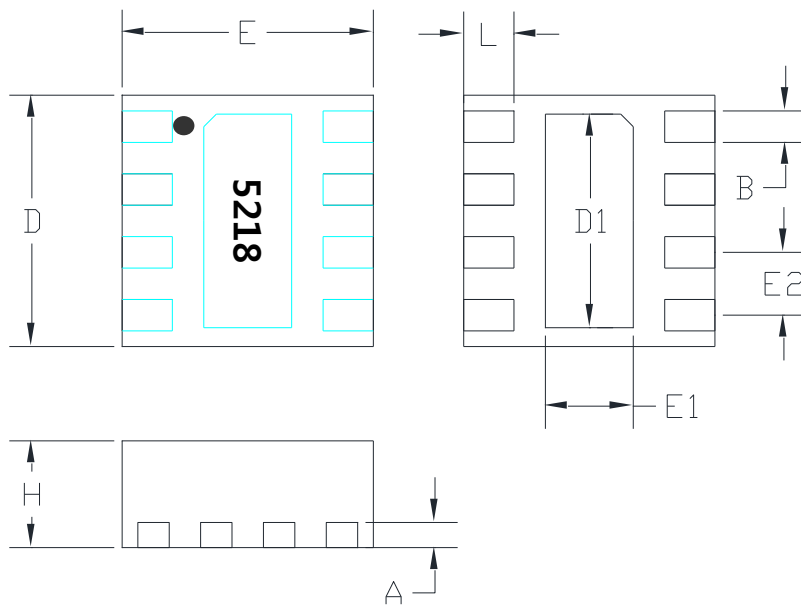
2) OIP3 is measured with two tones at the output power of +0 dBm/tone separated by 1 MHz.

5.3 Plot of S-parameters & Noise Figure



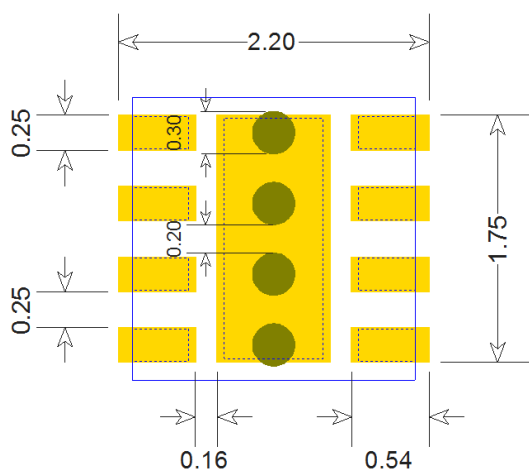


6. Package Outline (TDFN8)



Symbols	Dimensions (In mm)		
	MIN	NOM	MAX
A	-	0.20REF	-
B	0.18	0.23	0.28
D	1.95	2.00	2.03
D1	-	1.7BSC	-
E	1.95	2.00	2.03
E1	-	0.7BSC	-
E2	-	0.5BSC	-
L	0.35	0.40	0.45
H	0.80	0.85	0.90

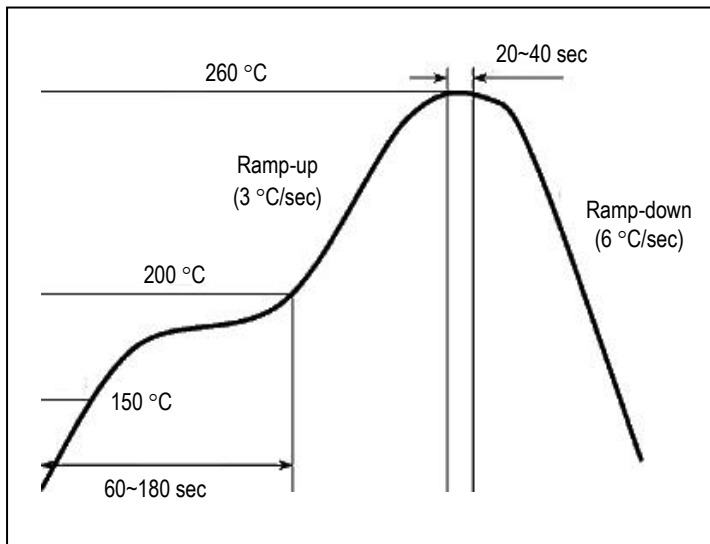
7. Surface Mount Recommendation (In mm)



NOTE

1. The number and size of ground via holes in a circuit board is critical for thermal and RF grounding considerations.
2. Recommend that the ground via holes be placed on the bottom of exposed pad of the device for better RF and thermal performance, as shown in the drawing at the left side.

8. Recommended Soldering Reflow Profile



(End of Datasheet)

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